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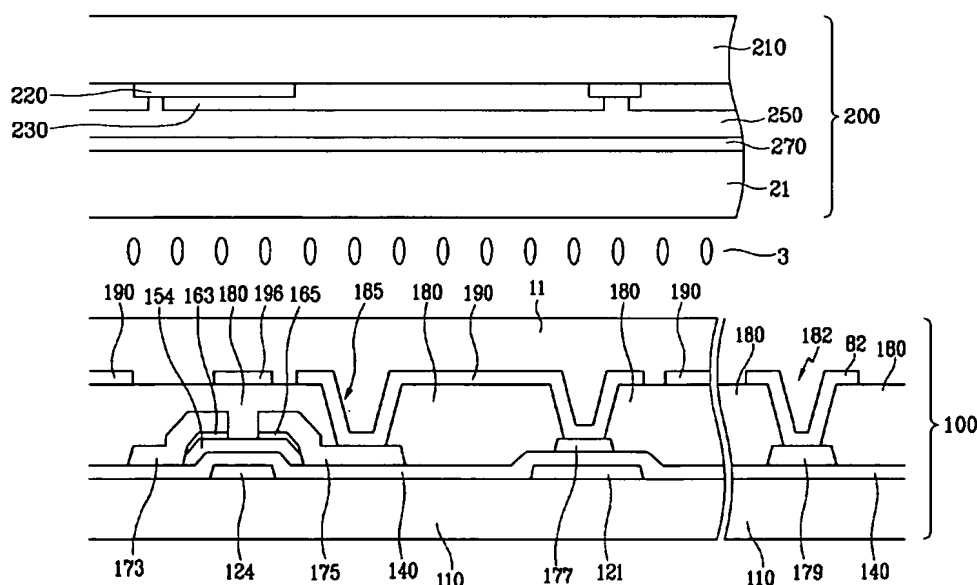
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(54) Title: THIN FILM TRANSISTOR, THIN FILM TRANSISTOR ARRAY PANEL, AND DISPLAY DEVICE



(57) Abstract: A thin film transistor is provided, which includes: a gate electrode (124); a gate insulating layer (140) formed on the gate electrode; a semiconductor layer (154) formed on the gate insulating layer and disposed opposite the gate electrode; a source electrode (173) and a drain electrode (175) that are formed at least in part on the semiconductor layer and face each other; a passivation layer (180) formed on the source electrode, the drain electrode, and a portion of the semiconductor layer that is not covered with the source electrode and the drain electrode; and a shielding electrode (196) formed on the passivation layer and disposed on a region between the source electrode and the drain electrode.

WO 2005/036653 A1



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